





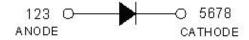
## ST2050DJF SCHOTTKY RECTIFIER



### **Features**

- Ultralow forward voltage drop
- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low thermal resistance
- · Avalanche capability specified
- Terminals finish: 100% Pure Tin
- Thin package: 1 mm
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	50	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	T <sub>C</sub> =118°C, In DC	20	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>C</sub> = 25 °C	250	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	<ul><li>@ 10A, Pulse, T<sub>J</sub> = 25 °C</li><li>@ 20A, Pulse, T<sub>J</sub> = 25 °C</li></ul>	0.47 0.52	- 0.65	V
	V <sub>F2</sub>	@ 10A, Pulse, T <sub>J</sub> = 125 °C @ 20A, Pulse, T <sub>J</sub> = 125 °C	0.38 0.48	- 0.60	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	0.03	4	mA
Reverse Current*	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	30	180	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	1300	-	pF

Pulse width < 300 μs, duty cycle < 2%



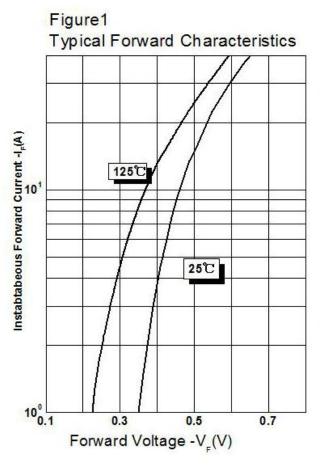


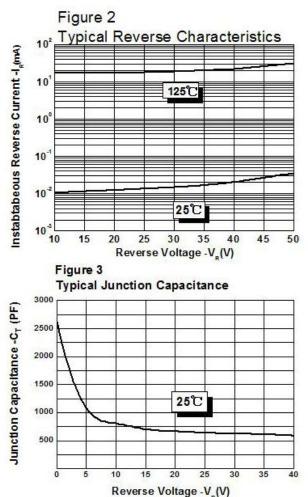


## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> Jc	DC operation	2.5	°C/W
Approximate Weight	wt	-	0.095	g

## **Ratings and Characteristics Curves**





<sup>•</sup> China - Germany - Korea - Singapore - United States •

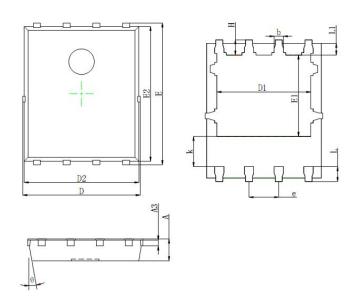
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •



# RoHS Po

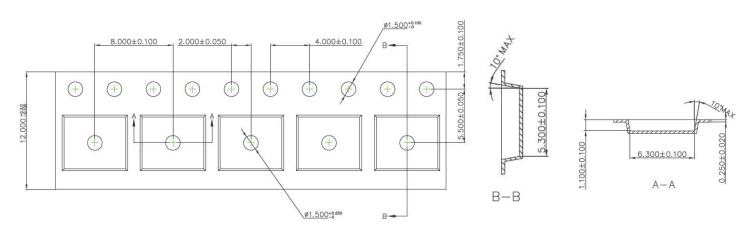


### **Mechanical Dimensions PDFNWB5×6-8L**



SYMBOL	Millimeters		Inches		
STIVIBUL	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.254 REF.		0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270 TYP.		0.050 TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
Θ	10°	12°	10°	12°	

## Carrier Tape Specification PDFNWB5×6-8L(mm)

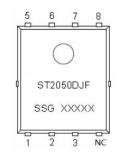


# **Ordering Information**

Device	Package	Shipping		
ST2050DJF	PDFNWB5×6-8L	3000 pcs / reel		
312000DJF	(Pb-Free)	3000 pcs / reer		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



### Where XXXXX is YYWWL

= Device Type = Forward Current (20A) ST 20 = Reverse Voltage (50) = Package type 50 DJF SSG = SSG = Year ww = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •







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